bh Fh ne

mk l

- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology, which provide high reliability

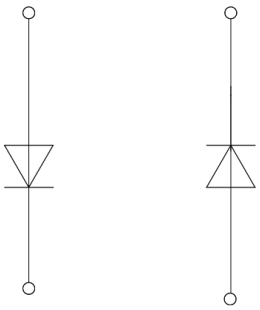
l kh n mL nf f kr

l k f mk	O en	gbm
V_{RRM}	1600	V
$I_{F(AV)}$(@ T_C = 100℃)	120	A
I_{FSM}(@ t_P = 10ms)	3360	A
V_F(Max)	1.60	V

i i eb mbhgl

- AC converter
- Inverter
- DC motor





lhemm F bf nf K mbg l (@ T_C = 25℃ unless otherwise specified)

l k f mk	hg bbhgl	Lr f he	O en l	gbm
Repetitive peak reverse voltage	T_{vj} = 25℃	V_{RRM}	1600	V
Non-repetitive peak reverse voltage	T_{vj} = 25℃	V_{RSM}	1700	V
Average forward current	T_C = 100℃	$I_{F(AV)}$	120	A
Forward surge current	1/2 cycle, Sine wave, 50Hz	I_{FSM}	3360	A
I^2t value for fusing	T_{vj} = 25℃	I^2t	56400	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

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e mkb e a k mkdomol (@ T_C = 25℃ unless otherwise specified)

l k f mk	hg bthgl	Lrf he	O en l			glbm
			F lg	Mri	F	
Peak forward voltage	I_F=360A, t_P=380μs	V_F			1.60	V
Reverse leakage current	$V_R = V_{RRM}$, T_{vj} = 25℃	I_{RRM}			100	μA
	$V_R = V_{RRM}$, T_{vj} = 150℃				40	mA
Threshold voltage	T_{vj} = 150℃, for power loss calculation only	V_{TO}			0.85	V
Dynamic resistance		r_T			1.5	mΩ

Ma kf e a k mkdomol (@ T_C = 25℃ unless otherwise specified)

l k f mk	hg bthgl	Lrf he	O en l			glbm
			F lg	Mri	F	
Thermal resistance, junction to case	per diode	$R_{th(j-c)}$		0.29		/W
Thermal resistance, case to heatsink	per diode	$R_{th(c-s)}$		0.12		/W
Mounting torque	Module and heatsink fixed torque M5	M	1.7		2.3	N·m

Hk kdg Bghkf mbhg

ob	F kdlg	l d	P b am	Bgg k h	l k kmhg
JMD120K316V1W	JMD120K316V1W	V1	43g/PCS	60 PCS	360 PCS

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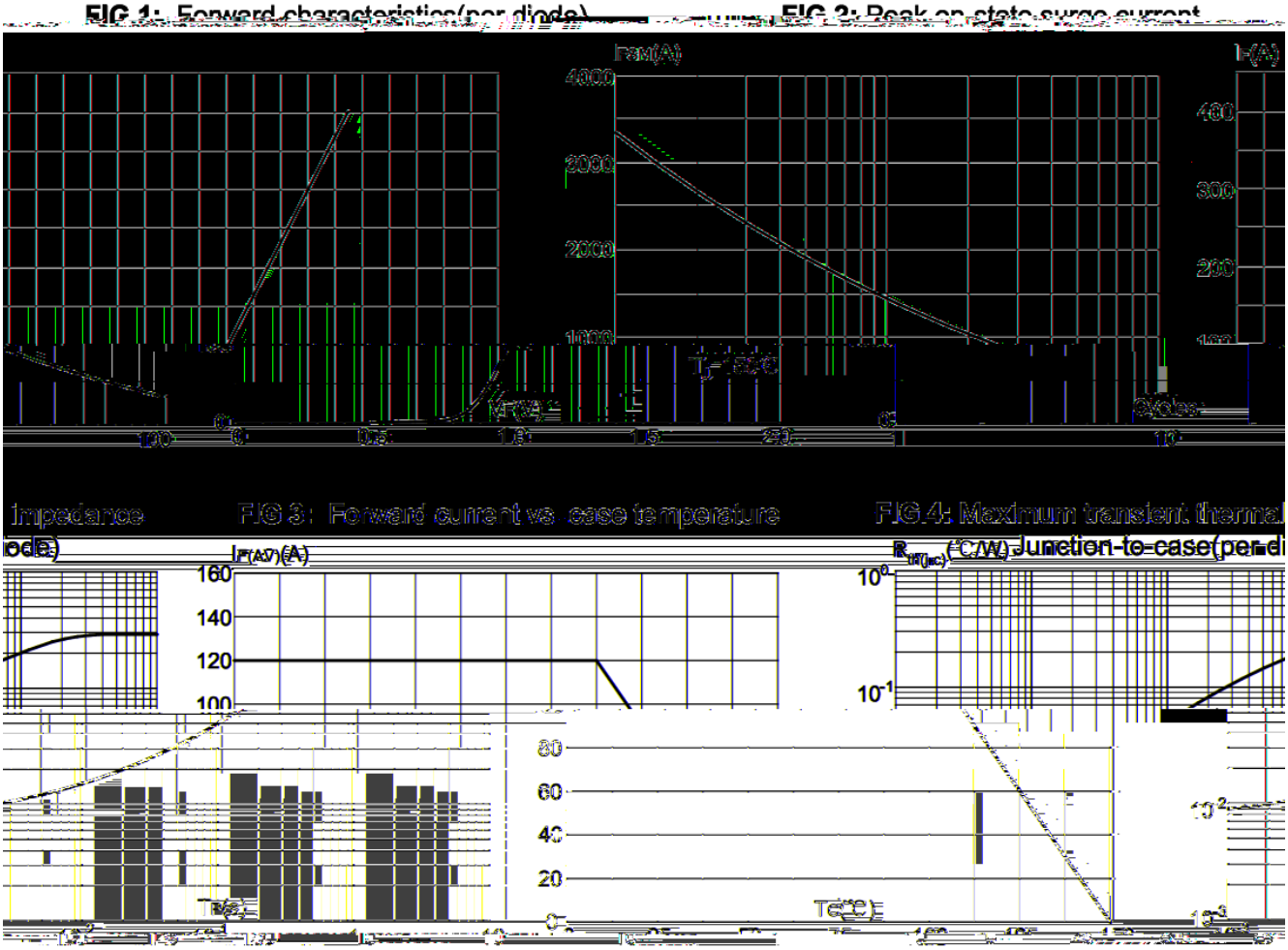
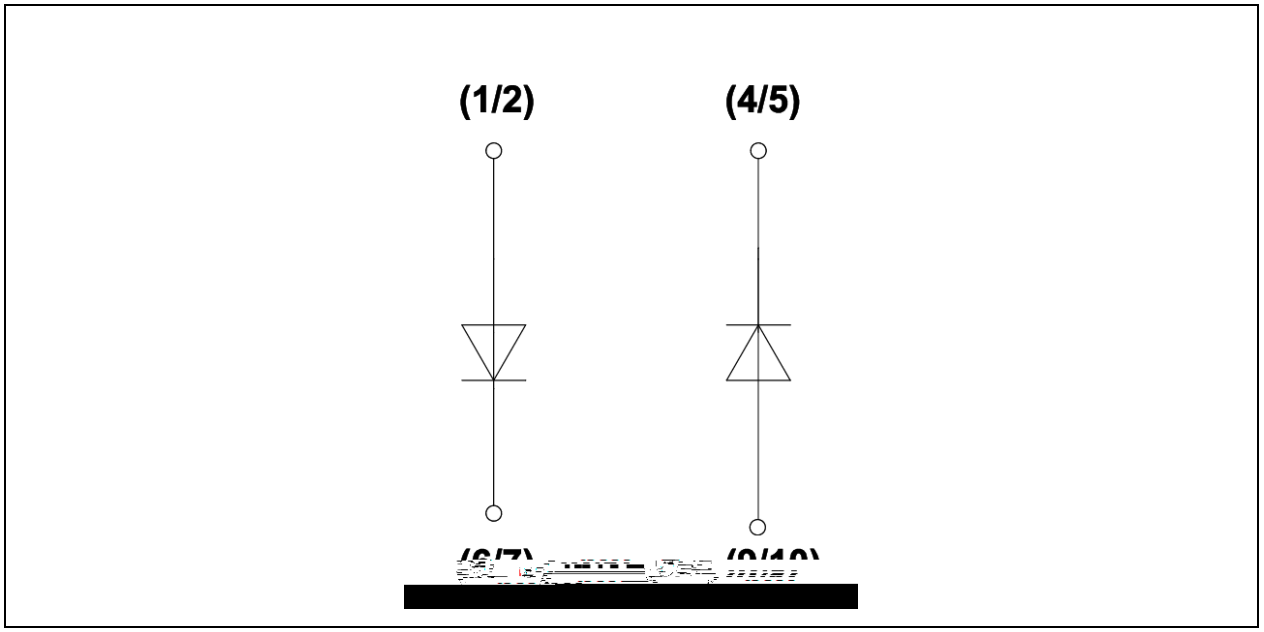
Mr i b e e mb e Ma kf e a k mkb mb l

FIG 1: Forward characteristics(per diode) FIG 2: Peak on-state surge current



bk nbm b k f



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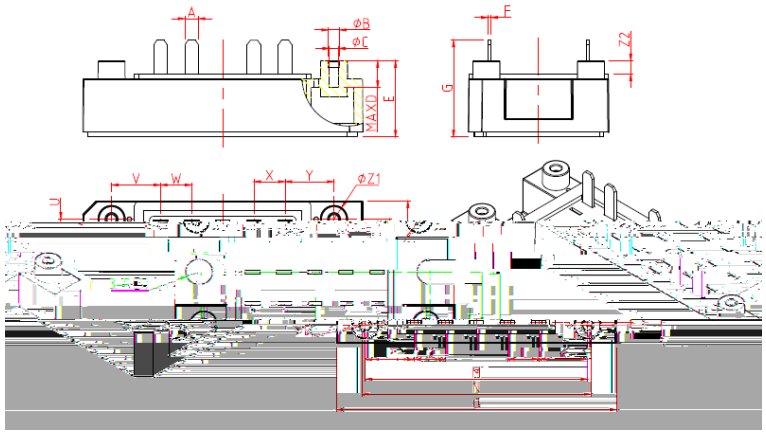
l d Hnndg l !f f "



Unit of measurement: mm

Ref	Dimensions					
	Millimeters			Inches		
	Min	Typ	Max	Min	Typ	Max
A	2.85	3	3.15	0.112	0.118	0.124
B	2.3	2.5	2.7	0.091	0.098	0.106
C	1.9	2.1	2.3	0.075	0.083	0.091
D			6			0.236
E	16.25	17	17.75	0.640	0.669	0.699
F	0.55	0.65	0.75	0.022	0.026	0.030
G	20.85	21.6	22.35	0.821	0.850	0.880

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